## 1.5-Gbps $2 \times 2$ LVDS CROSSPOINT SWITCH

## FEATURES

- Designed for Signaling Rates( ${ }^{1}$ ) Up To 1.5 Gbps
- Total Jitter < 65 ps
- Pin-Compatible With SN65LVDS22 and SN65LVDM22
- 25 mV of Receiver Input Threshold Hysteresis Over 0-V to 4-V Common-Mode Range
- Inputs Electrically Compatible With CML, LVPECL and LVDS Signal Levels
- Propagation Delay Times, 900 ps Maximum
- LVDT Integrates 110- $\Omega$ Terminating Resistor
- Offered in SOIC and TSSOP


## APPLICATIONS

- 10-G (OC-192) Optical Modules
- 622 MHz Central Office Clock Distribution
- Wireless Basestations
- Low Jitter Clock Repeater/Multiplexer
- Protection Switching for Serial Backplanes


## DESCRIPTION

The SN65LVDS122 and SN65LVDT122 are crosspoint switches that use low voltage differential signaling (LVDS) to achieve signaling rates as high as 1.5 Gbps. They are pin-compatible speed upgrades to the SN65LVDS22 and SN65LVDM22. The internal signal paths maintain differential signaling for high speeds and low signal skews. These devices have a 0 V to 4 V common-mode input range that accepts LVDS, LVPECL, CML inputs. Two logic pins (S0 and S1) set the internal configuration between the differential inputs and outputs. This allows the flexibility to perform the following configurations: $2 \times 2$ crosspoint switch, 2:1 mux, 1:2 splitter or dual repeater/translator within a single device. Additionally, SN65LVDT122 incorporates a 110- $\Omega$ termination resistor for those applications where board space is a premium. Although these devices are designed for 1.5 Gbps , some applications at a 2-Gbps data rate can be supported depending on loading and signal quality.

The intended application of this device is ideal for loopback switching for diagnostic routines, fanout buffering of clock/data distribution provide protection in fault-tolerant systems, clock muxing in optical modules, and for overall signal boosting over extended distances.

The SN65LVDS122 and SN65LVDT122 are characterized for operation from $-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$.


EYE PATTERNS OF OUTPUTS OPERATING SIMULTANEOUSLY


Horizontal Scale= $\mathbf{2 0 0}$ ps/div

[^0] storage or handling to prevent electrostatic damage to the MOS gates.

## ORDERING INFORMATION

| PACKAGE | TERMINATION <br> RESISTOR | PART NUMBER(1) | SYMBOLIZATION |
| :---: | :---: | :--- | :--- |
| SOIC | No | SN65LVDS122D | LVDS122 |
| SOIC | Yes | SN65LVDT122D | LVDT122 |
| TSSOP | No | SN65LVDS122PW | LVDS122 |
| TSSOP | Yes | SN65LVDT122PW | LVDT122 |

(1) Add the suffix R for taped and reeled carrier

## ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted(1)

(1) Stressesbeyondthose listedunder "absolute maximum ratings" may causepermanentdamage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.
(3) Tested in accordance with JEDEC Standard 22, Test Method A114-A.7.
(4) Tested in accordance with JEDEC Standard 22, Test Method C101.

## RECOMMENDED OPERATING CONDITIONS



## PACKAGE DISSIPATION RATINGS

| PACKAGE | $\mathrm{T}_{\mathrm{A}} \leq 25^{\circ} \mathrm{C}$ <br> POWER RATING | DERATING FACTOR(1) ABOVE $\mathrm{T}_{\mathrm{A}}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ | $\mathrm{T}_{\mathrm{A}}=85^{\circ} \mathrm{C}$ <br> POWER RATING |
| :---: | :---: | :---: | :---: |
| PW | 774 mW | $6.2 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ | 402 mW |
| D | 950 mW | $7.6 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ | 494 mW |

[^1]INPUT ELECTRICAL CHARACTERISTICS
over recommended operating conditions (unless otherwise noted)

| PARAMETER |  | TEST CONDITIONS | MIN | TYP(1) | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {IT }+}$ | Positive-going differential input voltage threshold | See Figure 1 and Table 1 |  |  | 100 | mV |
| VIT- | Negative-goingdifferential input voltage threshold | See Figure 1 and Table 1 | -100(2) |  |  | mV |
| VID(HYS) | Differential input voltage hysteresis $\left(\mathrm{V}_{\mathrm{IT}+}-\mathrm{V}_{\mathrm{IT}-}\right)$ |  |  | 25 |  | mV |
| ${ }^{\mathrm{IIH}}$ | High-level input current | $\mathrm{V}_{\mathrm{IH}}=2$ | -10 |  | 0 | $\mu \mathrm{A}$ |
|  |  |  | 0 |  | 20 |  |
| IIL | Low-level input current | V IL $=0.8 \mathrm{~V}$ | -10 |  | 0 | $\mu \mathrm{A}$ |
|  |  |  |  |  | 20 |  |
| ICC | Supply current | $\mathrm{R}_{\mathrm{L}}=100 \Omega$ |  | 80 | 100 | mA |
|  |  | Disabled |  | 35 | 45 |  |
| 1 | Input current (A or B inputs 'LVDS) | $\mathrm{V}_{\mathrm{I}}=0 \mathrm{~V}$ or 2.4 V , Other input at 1.2 V | -20 |  | 20 | $\mu \mathrm{A}$ |
|  |  | $\mathrm{V}_{\mathrm{I}}=4 \mathrm{~V}$, Other input at 1.2 V | 0 |  | 33 |  |
|  | Input current (A or B inputs 'LVDT) | $\mathrm{V}_{\mathrm{I}}=0 \mathrm{~V}$ or 2.4 V , Other input open | -40 |  | 40 | $\mu \mathrm{A}$ |
|  |  | $\mathrm{V}_{\mathrm{I}}=4 \mathrm{~V}$, Other input open | 0 |  | 66 |  |
| ${ }_{1}$ (OFF) | Input current (A or B inputs 'LVDS) | $\mathrm{V}_{C C}=1.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{I}}=0 \mathrm{~V} \text { or } 2.4 \mathrm{~V} \text {, }$ <br> Other input at 1.2 V | -20 |  | 20 | $\mu \mathrm{A}$ |
|  |  | $\mathrm{V}_{\mathrm{CC}}=1.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{I}}=2.4 \mathrm{~V} \text { or } 4 \mathrm{~V},$ <br> Other input at 1.2 V | 0 |  | 33 |  |
|  | Input current (A or B inputs 'LVDT) | $\mathrm{V}_{\mathrm{C}}=1.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{I}}=0 \mathrm{~V}$ or 2.4 V , Other input open | -40 |  | 40 | $\mu \mathrm{A}$ |
|  |  | $\mathrm{V}_{\mathrm{CC}}=1.5 \mathrm{~V}, \mathrm{~V}_{\mathrm{I}}=2.4 \mathrm{~V}$ or 4 V , Other input open | 0 |  | 66 |  |
| 1 l | Input offset current (\| $\mathrm{I}_{\mathrm{IA}}-\mathrm{I}_{\mathrm{IB}} \mid$ ) $\quad$ 'LVDS | $\mathrm{V}_{\text {IA }}=\mathrm{V}_{\text {IB }}, 0 \leq \mathrm{V}_{\text {IA }} \leq 4 \mathrm{~V}$ | -6 |  | 6 | $\mu \mathrm{A}$ |
| $\mathrm{R}_{\mathrm{T}}$ | Termination resistance ('LVDT) |  | 90 | 110 | 132 | $\Omega$ |
|  | Termination resistance ('LVDT with power-off) | $\mathrm{V}_{\mathrm{ID}}=300 \mathrm{mV}$ and 500 mV , <br> $\mathrm{V}_{\mathrm{CC}}=1.5 \mathrm{~V}, \quad \mathrm{~V}_{\text {IC }}=0 \mathrm{~V}$ to 2.4 V | 90 | 110 | 132 |  |
| $\mathrm{Cl}_{1}$ | Differential input capacitance ('LVDT with power-off) | $\mathrm{V}_{\mathrm{I}}=0.4 \sin (4 \mathrm{E} 6 \pi \mathrm{t})+0.5 \mathrm{~V}$ |  | 3 |  | pF |
|  |  | Powered down |  | 3 |  |  |

(1) All typical values are at $25^{\circ} \mathrm{C}$ and with a $3.3-\mathrm{V}$ supply.
(2) The algebraic convention in which the least positive (most negative) limit is designated as minimum is used in this data sheet.

OUTPUT ELECTRICAL CHARACTERISTICS
over recommended operating conditions (unless otherwise noted)

|  | PARAMETER | TEST CONDITIONS | MIN | TYP(1) | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| \|VODI | Differential output voltage magnitude | See Figure 2 | 247 | 310 | 454 |  |
| $\Delta \mathrm{V}_{\text {ODI }}$ | Change in differential output voltage magnitude between logic states | $V_{I D}= \pm 100 \mathrm{mV}, \mathrm{See}$ Figure 2 | -50 |  | 50 | mV |
| VOC(SS) | Steady-state common-mode output voltage | See Figure 3 | 1.125 |  | 1.375 | V |
| $\triangle \mathrm{VOC}(\mathrm{SS})$ | Change in steady-state common-mode output voltage between logic states |  | -50 |  | 50 | mV |
| V OC(PP) | Peak-to-peak common-mode output voltage |  |  | 50 | 150 | mV |
| los | Short-circuit output current | $\mathrm{V}_{\mathrm{O}(\mathrm{Y})}$ or $\mathrm{V}_{\mathrm{O}(\mathrm{Z})}=0 \mathrm{~V}$ | -24 |  | 24 | mA |
| $\operatorname{los}(\mathrm{D})$ | Differential short-circuit output current | $\mathrm{V}_{\mathrm{OD}}=0 \mathrm{~V}$ | -12 |  | 12 | mA |
| ${ }^{\text {loz }}$ | High-impedance outputcurrent | $\mathrm{V}_{\mathrm{OD}}=600 \mathrm{mV}$ | -1 |  | 1 | $\mu \mathrm{A}$ |
|  |  | $\mathrm{V}_{\mathrm{O}}=0 \mathrm{~V}$ or $\mathrm{V}_{\mathrm{CC}}$ | -1 |  | 1 |  |
| $\mathrm{C}_{0}$ | Differential output capacitance | $\mathrm{V}_{\mathrm{I}}=0.4 \sin (4 \mathrm{E} 6 \pi \mathrm{t})+0.5 \mathrm{~V}$ |  | 3 |  | pF |

(1) All typical values are at $25^{\circ} \mathrm{C}$ and with a $3.3-\mathrm{V}$ supply.

## TIMING SPECIFICATIONS

|  | PARAMETER | TEST CONDITIONS | MIN | NOM | MAX |
| :--- | :--- | ---: | ---: | :---: | :---: |
| UNIT |  |  |  |  |  |
| tSET | Input to select setup time |  | 0 |  |  |
| tHOLD | Input to select hold time |  | $n s$ |  |  |
| tSWITCH | Select to switch output |  | 0.5 |  | $n$ |

## SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

|  | PARAMETER | TEST CONDITIONS | MIN | NOM(1) | MAX | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| tple | Propagation delay time, low-to-high-level output | See Figure 4 | 400 | 650 | 900 | ps |
| tPHL | Propagation delay time, high-to-low-level output |  | 400 | 650 | 900 | ps |
| $\mathrm{tr}_{r}$ | Differential output signal rise time ( $20 \%-80 \%$ ) |  |  |  | 280 | ps |
| $\mathrm{tf}_{\mathrm{f}}$ | Differential output signal fall time (20\%-80\%) |  |  |  | 280 | ps |
| tsk(p) | Pulse skew (\|tPHL - tPLH|) ${ }^{(2)}$ |  |  | 10 | 50 | ps |
| $\mathrm{t}_{\text {sk( }}$ (pp) | Part-to-partskew(3) | $\mathrm{V}_{\text {ID }}=0.2 \mathrm{~V}$ |  |  | 100 | ps |
| tjit(per) | Period jitter, rms (1 standard deviation) ${ }^{(4)}$ | 750 MHz clock input(5) |  | 1 | 2.2 | ps |
| tijit(cc) | Cycle-to-cycle jitter (peak) ${ }^{(4)}$ | 750 MHz clock input(6) |  | 10 | 17 | ps |
| tjit(pp) | Peak-to-peakjitter(4) | $\begin{aligned} & \hline 1.5 \text { Gbps } \\ & \text { 223-1 PRBS input } 7 \text { ) } \end{aligned}$ |  | 33 | 65 | ps |
| tjit(det) | Deterministicjitter, peak-to-peak(4) | $\begin{aligned} & \hline 1.5 \text { Gbps } \\ & 2^{7}-1 \text { PRBS input(8) } \end{aligned}$ |  | 17 | 50 | ps |
| tPHZ | Propagation delay time, high-level-to-high-impedance output | See Figure 5 |  | 6 | 8 | ns |
| tpLZ | Propagation delay time, low-level-to-high-impedance output | See Figure 5 |  | 6 | 8 | ns |
| tPZH | Propagation delay time, high-impedance-to-high-level output | See Figure 5 |  | 4 | 6 | ns |
| tPZL | Propagation delay time, high-impedance-to-low-level output | See Figure 5 |  | 4 | 6 | ns |
| tsk(0) | Output Skew(9) |  |  | 15 | 40 | ps |

(1) All typical values are at $25^{\circ} \mathrm{C}$ and with a $3.3-\mathrm{V}$ supply.
(2) $\mathrm{t}_{\mathrm{sk}}(\mathrm{p})$ is the magnitude of the time difference between the TPLH $^{\text {and }} \mathrm{TPHL}^{\text {of }}$ of any output of a single device.
${ }^{(3)} \mathrm{t}_{\mathrm{sk}}(\mathrm{pp})$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.
(4) Jitter is ensured by design and characterization. Stimulus jitter has been subtracted from the numbers.
(5) Input voltage $=V_{I D}=200 \mathrm{mV}, 50 \%$ duty cycle at $750 \mathrm{MHz}, \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=50 \mathrm{ps}(20 \%$ to $80 \%)$, measured over 1000 samples.
(6) Input voltage $=V_{I D}=200 \mathrm{mV}, 50 \%$ duty cycle at $750 \mathrm{MHz}, \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=50 \mathrm{ps}(20 \%$ to $80 \%)$.
(7) Input voltage $=V_{I D}=200 \mathrm{mV}, 2^{23}-1$ PRBS pattern at $1.5 \mathrm{Gbps}, \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=50 \mathrm{ps}(20 \%$ to $80 \%)$, measured over 200 k samples.
(8) Input voltage $=V_{I D}=200 \mathrm{mV}, 2^{7}-1$ PRBS pattern at $1.5 \mathrm{Gbps}, \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=50 \mathrm{ps}(20 \%$ to $80 \%)$.
(9) Output skew is the magnitude of the time delay difference between the outputs of a single device with all inputs tied together.

## PIN ASSIGNMENTS

```
D OR PW PACKAGE
(TOP VIEW)
```

| $1 \mathrm{~B} \square$ | 10 | 16 | $\square V_{C C}$ |
| :---: | :---: | :---: | :---: |
| 1A $\square$ | 2 | 15 | $\square V_{C C}$ |
| S0 $\square$ | 3 | 14 | $\square 1 \mathrm{Y}$ |
| 1DE ■ | 4 | 13 | $\square 1 \mathrm{C}$ |
| S1 $\square$ | 5 | 12 | $\square$ 2DE |
| 2A $\square$ | 6 | 11 | $\square 2 Z$ |
| 2B $\square$ | 7 | 10 | 2Y |
| GND ■ | 8 | 9 | $\square$ GND |

CROSSPOINT LOGIC TABLE

| $\mathbf{S 1}$ | $\mathbf{S 0}$ | $\mathbf{1 Y} / \mathbf{1 Z}$ | $\mathbf{2 Y} / \mathbf{2 Z}$ | FUNCTION |
| :---: | :---: | :---: | :---: | :---: |
| 0 | 0 | $1 \mathrm{~A} / 1 \mathrm{~B}$ | $1 \mathrm{~A} / 1 \mathrm{~B}$ | splitter |
| 0 | 1 | $2 \mathrm{~A} / 2 \mathrm{~B}$ | $2 \mathrm{~A} / 2 \mathrm{~B}$ | splitter |
| 1 | 0 | $1 \mathrm{~A} / 1 \mathrm{~B}$ | $2 \mathrm{~A} / 2 \mathrm{~B}$ | router |
| 1 | 1 | $2 \mathrm{~A} / 2 \mathrm{~B}$ | $1 \mathrm{~A} / 1 \mathrm{~B}$ | router |

PARAMETER MEASUREMENT INFORMATION


Figure 1. Voltage and Current Definitions


Figure 2. Differential Output Voltage ( $\mathrm{V}_{\mathrm{OD}}$ ) Test Circuit


NOTE: All input pulses are supplied by a generator having the following characteristics: $\mathrm{t}_{\mathrm{r}}$ or $\mathrm{t}_{\mathrm{f}} \leq 0.25 \mathrm{~ns}$, pulse repetition rate (PRR) $=0.5 \mathrm{Mpps}$, pulsewidth $=500 \pm 10 \mathrm{~ns} ; \mathrm{R}_{\mathrm{L}}=100 \Omega ; \mathrm{C}_{\mathrm{L}}$ includes instrumentation and fixture capacitance within $0,06 \mathrm{~mm}$ of the D.U.T.; the measurement of $\mathrm{V}_{\mathrm{OC}}(\mathrm{PP})$ is made on test equipment with a -3 dB bandwidth of at least 300 MHz .

Figure 3. Test Circuit and Definitions for the Driver Common-Mode Output Voltage


NOTE: All input pulses are supplied by a generator having the following characteristics: $\mathrm{t}_{\mathrm{r}}$ or $\mathrm{t}_{\mathrm{f}} \leq 0.25 \mathrm{~ns}$, pulse repetition rate (PRR) $=0.5 \mathrm{Mpps}$, pulsewidth $=500 \pm 10 \mathrm{~ns} . C_{L}$ includes instrumentation and fixture capacitance within $0,06 \mathrm{~mm}$ of the D.U.T.

Figure 4. Timing Test Circuit and Waveforms


NOTE:
All input pulses are supplied by a generator having the following characteristics: $t_{r}$ or $t_{f} \leq 1 \mathrm{~ns}$, pulse repetition rate $(P R R)=0.5 \mathrm{Mpps}$, pulsewidth $=500 \pm 10 \mathrm{~ns} . C_{L}$ includes instrumentation and fixture capacitance within $0,06 \mathrm{~mm}$ of the D.U.T.

Figure 5. Enable and Disable Time Circuit and Definitions


Figure 6. Example Switch, Setup, and Hold Times
$\mathrm{t}_{\text {(SET) }}$ and $\mathrm{t}_{\text {(HOLD) }}$ times specify that data must be in a stable state before and after mux control switches.
Table 1. Receiver Input Voltage Threshold Test

| APPLIED VOLTAGES |  | RESULTING DIFFERENTIAL <br> INPUT VOLTAGE | RESULTING COMMON- <br> MODE INPUT VOLTAGE | OUTPUT |
| :---: | :---: | :---: | :---: | :---: |
| $\mathbf{V}_{\mathbf{I A}}$ | $\mathbf{V}_{\mathbf{I B}}$ | $\mathbf{V}_{\mathbf{I D}}$ | $\mathbf{V}_{\mathbf{I C}}$ |  |
| 1.25 V | 1.15 V | 100 mV | 1.2 V | H |
| 1.15 V | 1.25 V | -100 mV | 1.2 V | L |
| 4.0 V | 3.9 V | 100 mV | 3.95 V | H |
| 3.9 V | 4.0 V | -100 mV | 3.95 V | L |
| 0.1 V | 0.0 V | 100 mV | 0.05 V | H |
| 0.0 V | 0.1 V | -100 mV | 0.05 V | L |
| 1.7 V | 0.7 V | 1000 mV | 1.2 V | H |
| 0.7 V | 1.7 V | -1000 mV | 1.2 V | L |
| 4.0 V | 3.0 V | 1000 mV | 3.5 V | H |
| 3.0 V | 4.0 V | -1000 mV | 3.5 V | L |
| 1.0 V | 0.0 V | 1000 mV | 0.5 V | H |
| 0.0 V | 1.0 V | -1000 mV | 0.5 V | L |

$\mathrm{H}=$ high level, $\mathrm{L}=$ low level

## EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS

INPUT LVDS122


OUTPUT LVDS122


## TYPICAL CHARACTERISTICS



Figure 7


Figure 10

PEAK-TO-PEAK JITTER
vs
DATA RATE


Figure 13

DIFFERENTIAL PROPAGATION DELAY
vs
COMMON-MODE INPUT VOLTAGE


Figure 8

PEAK-TO-PEAK JITTER
vs
DATA RATE


Figure 11

PEAK-TO-PEAK JITTER
VS
FREQUENCY


Figure 14

DIFFERENTIAL PROPAGATION DELAY
VS
TEMPERATURE


Figure 9

PEAK-TO-PEAK JITTER
vs
FREQUENCY


Figure 12

PEAK-TO-PEAK JITTER
vS
DATA RATE


Figure 15


Figure 16


LVDS122
622 Mbps, $2{ }^{23}$ - 1 PRBS


Horizontal Scale= $\mathbf{2 0 0} \mathrm{ps} /$ div
LVDS-to-LVDS
Figure 19

LVDS122
1.5 Gbps, $2^{23}$ - 1 PRBS


Horizontal Scale= $\mathbf{1 0 0} \mathrm{ps} / \mathrm{div}$ LVDS-to-LVDS
Figure 20


Figure 21. Jitter Setup Connections for SN65LVDS122

## APPLICATION INFORMATION

TYPICAL APPLICATION CIRCUITS (ECL, PECL, LVDS, ETC.)


Figure 22. Low-Voltage Positive Emitter-Coupled Logic (LVPECL)


Figure 23. Common-Mode Logic (CML)


Figure 24. Single-Ended (LVPECL)


Figure 25. Low-Voltage Differential Signaling (LVDS)


Figure 26. AC-Coupled Between ECL and LVDS or LVPECL


Figure 27. $2 \times 2$ Crosspoint


Figure 28. 1:2 Spitter


Figure 29. Dual Repeater


Figure 30. 2:1 MUX

## MECHANICAL DATA

D (R-PDSO-G**) PLASTIC SMALL-OUTLINE
PACKAGE
8 PINS SHOWN


| PIMS ** | 8 | 14 | 16 |
| :---: | :---: | :---: | :---: |
| A MAX | 0.197 <br> $(5,00)$ | 0.344 <br> $(8,75)$ | 0.394 <br> $(10,00)$ |
|  | 0.189 <br> $(4,80)$ | 0.337 <br> $(8,55)$ | 0.386 <br> $(9,80)$ |

4040047/E09/01
NOTES:A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed $0.006(0,15)$.
D. Falls within JEDEC MS-012

## MECHANICAL DATA

PW (R-PDSO-G**)


| PINS ** | $\mathbf{8}$ | $\mathbf{1 4}$ | $\mathbf{1 6}$ | $\mathbf{2 0}$ | $\mathbf{2 4}$ | $\mathbf{2 8}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| A MAX | 3,10 | 5,10 | 5,10 | 6,60 | 7,90 | 9,80 |
| A MIN | 2,90 | 4,90 | 4,90 | 6,40 | 7,70 | 9,60 |

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. Falls within JEDEC MO-153

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[^0]:    Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.
    ${ }^{(1)}$ The signaling rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).

[^1]:    (1) This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

